

**TRANSMITTAL OF FORMAL DRAWINGS**Docket No.
YOR920030323US1 (16890)Invention Application Of: **Diane C. Boyd, et al.**

| Serial No. | Filing Date | Confirmation No. | Examiner | Art Unit |
|------------|------------------|------------------|------------|------------|
| 10/725,849 | December 2, 2003 | Unassigned | Unassigned | Unassigned |

Invention: **ULTRA-THIN Si CHANNEL MOSFET USING A SELF-ALIGNED OXYGEN IMPLANT AND DAMASCENE TECHNIQUE**Address to:
**Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450**

Transmitted herewith are:

6 sheets of formal drawing(s) for this application.☒ Each sheet of drawing indicates the identifying indicia suggested in 37 CFR Section 1.84(c).
Signature**Steven Fischman
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LSS:HAH:kc**Dated: **February 24, 2004**I certify that this document and attached formal drawings are being deposited on **February 24, 2004** with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.
Signature**Steven Fischman**

Typed or Printed Name